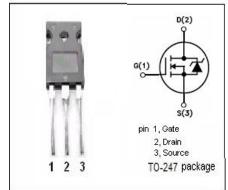


# isc N-Channel MOSFET Transistor

# **FCH041N60F**

## • FEATURES

- · With TO-247 packaging
- With low gate drive requirements
- · Easy to drive
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



## APPLICATIONS

· Switching applications



## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                                  | VALUE      | UNIT                 |  |
|------------------|--|------------|----------------------|--|
| V <sub>DSS</sub> | Drain-Source Voltage                       | 600        | V                    |  |
| V <sub>GSS</sub> | Gate-Source Voltage                        | ±20        | V                    |  |
| I <sub>D</sub>   | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | 76<br>48.1 | А                    |  |
| I <sub>DM</sub>  | Drain Current-Single Pulsed                | 228        | А                    |  |
| P <sub>D</sub>   | Total Dissipation                          | 595        | W                    |  |
| Tj               | Operating Junction Temperature             | -55~150    | $^{\circ}\mathbb{C}$ |  |
| T <sub>stg</sub> | Storage Temperature                        | -55~150    | ${\mathbb C}$        |  |

# 

|     | 100000000 |       |
|-----|-----------|-------|
| DIM | MIN       | MAX   |
| Α   | 19.80     | 20.20 |
| В   | 15.40     | 15.80 |
| C   | 4.90      | 5.10  |
| D   | 0.90      | 1.10  |
| E   | 1.40      | 1.60  |
| F   | 1.90      | 2.10  |
| G   | 10.80     | 11.00 |
| Н   | 2.40      | 2.60  |
| J   | 0.50      | 0.70  |
| K   | 19.50     | 20.50 |
| P   | 3.90      | 4.10  |
| Q   | 3.30      | 3.50  |
| U   | 5.20      | 5.40  |
| ٧   | 2.90      | 3.10  |

## • THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                          | MAX  | UNIT |
|-----------|------------------------------------|------|------|
| Rth(ch-c) | Channel-to-case thermal resistance | 0.21 | °C/W |

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# **FCH041N60F**

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                      | CONDITIONS   | MIN | ТҮР | MAX     | UNIT |
|---------------------|--------------------------------|--|-----|-----|---------|------|
| BV <sub>DSS</sub>   | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA   | 600 |     |         | V    |
| V <sub>GS(th)</sub> | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =0.25mA  | 3.0 |     | 5.0     | V    |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =38A   |     | 36  | 41      | mΩ   |
| I <sub>GSS</sub>    | Gate-Source Leakage Current    | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0V  |     |     | ±0.1    | μА   |
| I <sub>DSS</sub>    | Drain-Source Leakage Current   | V <sub>DS</sub> = 480V; V <sub>GS</sub> = 0V;@Tc=25°C<br>V <sub>DS</sub> = 480V; V <sub>GS</sub> = 0V;Tc=125°C |     |     | 1<br>10 | μА   |
| V <sub>SDF</sub>    | Diode forward voltage          | I <sub>SD</sub> =38A, V <sub>GS</sub> = 0 V  |     |     | 1.2     | V    |



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